	Hits	Search Text	DBs
1	1	((MIM with capacitor) same DRAM) and ((photo or imageable or resist) with (layer$4 or film$3 or form$4 or deposit$4)) and (copper or Cu) and ((metal$3 near oxide$2) same photo$3 same etch$4) and ((tantalum or Ta) same (Cu or copper))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	1	((MIM with capacitor) same DRAM) and ((photo or imageable or resist) with (layer$4 or film$3 or form$4 or deposit$4)) and (copper or Cu) and (metal$3 near $3oxide$2) and (photo same etch$4) and ((tantalum or Ta) same (Cu or copper))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	3	(MIM near2 capacitor) and DRAM and ((photo or imageable or resist) with (layer$4 or film$3 or form$4 or deposit$4)) and (copper or Cu) and (metal$3 near2 $3oxide$2) and (photo$4 same etch$4) and ((tantalum or Ta) same (Cu or copper))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	2	(MIM near2 capacitor) and DRAM and (photo or imageable or resist or photoresist) and (copper or Cu) and (metal$3 near2 $3oxide$2) and (photo$4 same etch$4 same pattern$4) and ((tantalum or Ta) same (Cu or copper or Ta$1Cu))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	2	(MIM near2 capacitor) and DRAM and (photo or imageable or resist or photoresist) and (copper or Cu) and ((metal$3 or Ta or Ti or Si$2) near2 $3oxide$2) and (photo$4 same etch$4) and (tantalum or Ta) and (Cu or copper or Ta$1Cu) and (TaN same sputter$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	2	(MIM near2 capacitor) and DRAM and (photo or imageable or resist or photoresist) and (copper or Cu) and ((metal$3 or Ta or Ti or Si$2) near2 $3oxide$2) and (photo$4 same etch$4) and (tantalum or Ta) and (Cu or copper or Ta$1Cu) and ((Ta$2N or (tantalum near3 nitride)) same sputter$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	1	(MIM near2 capacitor) and DRAM and (photo or imageable or resist or photoresist) and (copper or Cu) and ((a$3diamond or (black with diamond)) same (K or (absorption with coeff$5) or low$3K)) and (SiC or (silicon near3 carbide)) and (SiON or silicon$3oxy$2nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	1	(MIM near2 capacitor) and DRAM and (photo or imageable or resist or photoresist) and (copper or Cu) and ((a$3diamond or (black with diamond or diamond)) same (K or (absorption with coeff$5) or low$3K)) and (SiC or (silicon near3 carbide)) and (SiON or silicon$3oxy$2nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	1	(MIM near2 capacitor) and DRAM and (photo or imageable or resist or photoresist) and (copper or Cu) and (a$3diamond or (black with diamond) or diamond) and (K or (absorption with coeff$5) or low$3K) and (SiC or (silicon near3 carbide)) and (SiON or silicon$3oxy$2nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	2	(MIM near2 capacitor) and DRAM and (photo or imageable or resist or photoresist) and (copper or Cu) and (a$3diamond or (black with diamond) or diamond) and (K or (absorption with coeff$5) or low$3K or (low$2k near3 dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	2	(MIM near2 capacitor) and DRAM and (photo or imageable or resist or photoresist) and (copper or Cu) and (metal$3 near2 $3oxide$2) and (photo$4 same etch$4) and ((tantalum or Ta) same (Cu or copper or Ta$1Cu)) and TaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB